

Dual N-Channel 60-V (D-S), 175 °C MOSFET

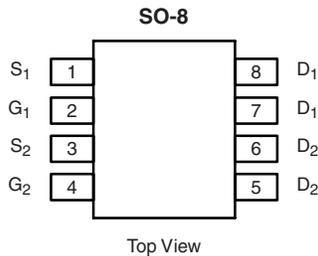
PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
60	0.080 at $V_{GS} = 10$ V	± 3.7
	0.100 at $V_{GS} = 4.5$ V	± 3.4

FEATURES

- TrenchFET® Power MOSFETs
- Maximum Junction Temperature: 175 °C Rated

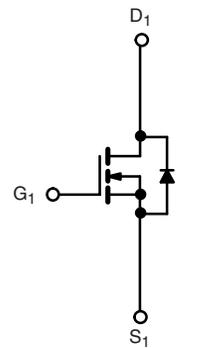


Available
RoHS*
COMPLIANT

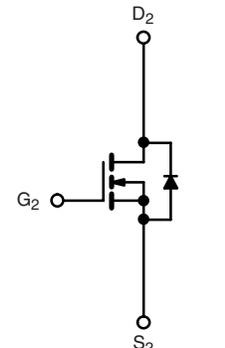


Ordering Information:

Si9945AEY-T1
Si9945AEY-T1-E3 (Lead (Pb)-free)



N-Channel MOSFET



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted				
Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V_{DS}	60	V	
Gate-Source Voltage	V_{GS}	± 20		
Continuous Drain Current ($T_J = 175$ °C) ^a	I_D	$T_A = 25$ °C	± 3.7	A
		$T_A = 70$ °C	± 3.2	
Pulsed Drain Current	I_{DM}	25		
Continuous Source Current (Diode Conduction) ^a	I_S	2		
Maximum Power Dissipation ^a	P_D	$T_A = 25$ °C	2.4	W
		$T_A = 70$ °C	1.7	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 175	°C	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typ	Max	Unit	
Junction-to-Ambient ^a	R_{thJA}	$t \leq 10$ sec	62.5	°C/W	
		Steady State	93		

Notes:

a. Surface Mounted on 1" x 1" FR4 Board.

* Pb containing terminations are not RoHS compliant, exemptions may apply.

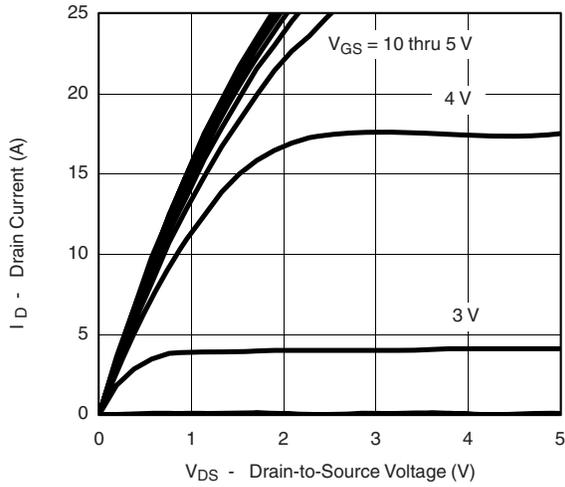
SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	1.0		3	V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\ \text{V}, V_{GS} = \pm 20\ \text{V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 60\ \text{V}, V_{GS} = 0\ \text{V}$			1	μA
		$V_{DS} = 60\ \text{V}, V_{GS} = 0\ \text{V}, T_J = 55\text{ }^\circ\text{C}$			10	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq 5\ \text{V}, V_{GS} = 10\ \text{V}$	20			A
Drain-Source On-State Resistance ^a	$r_{DS(on)}$	$V_{GS} = 10\ \text{V}, I_D = 3.7\ \text{A}$		0.06	0.080	Ω
		$V_{GS} = 4.5\ \text{V}, I_D = 3.4\ \text{A}$		0.075	0.100	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 15\ \text{V}, I_D = 3.7\ \text{A}$		11		S
Diode Forward Voltage ^a	V_{SD}	$I_S = 2.0\ \text{A}, V_{GS} = 0\ \text{V}$			1.2	V
Dynamic^b						
Total Gate Charge	Q_g	$V_{DS} = 30\ \text{V}, V_{GS} = 10\ \text{V}, I_D = 3.7\ \text{A}$		11	20	nC
Gate-Source Charge	Q_{gs}			2		
Gate-Drain Charge	Q_{gd}			2		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 30\ \text{V}, R_L = 30\ \Omega$ $I_D \cong 1\ \text{A}, V_{GEN} = 10\ \text{V}, R_G = 6\ \Omega$		9	20	ns
Rise Time	t_r			10	20	
Turn-Off Delay Time	$t_{d(off)}$			21	40	
Fall Time	t_f			8	20	
Source-Drain Reverse Recovery Time	t_{rr}	$I_F = 2.0\ \text{A}, di/dt = 100\ \text{A}/\mu\text{s}$		45	80	

Notes:

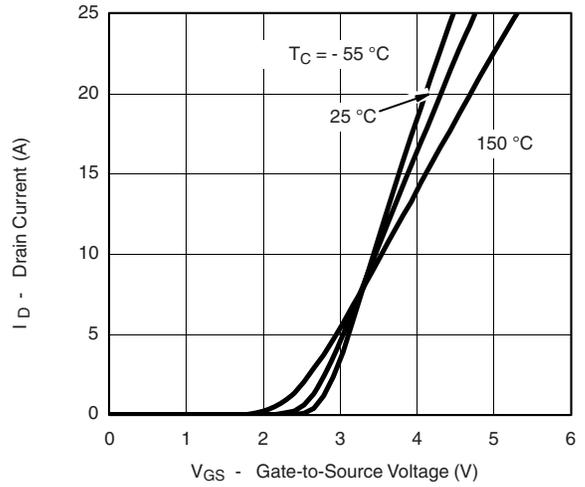
- a. Pulse test; pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

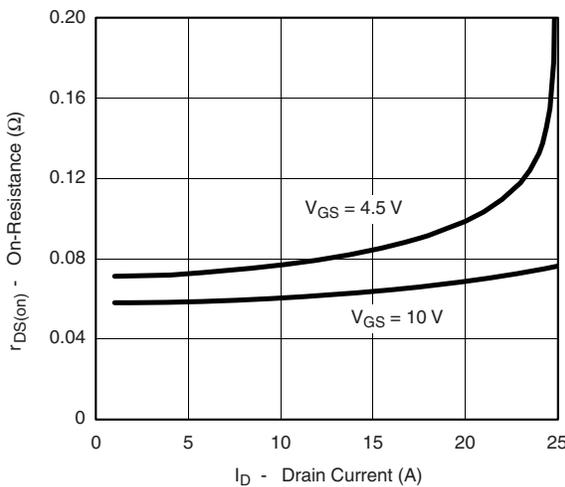
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



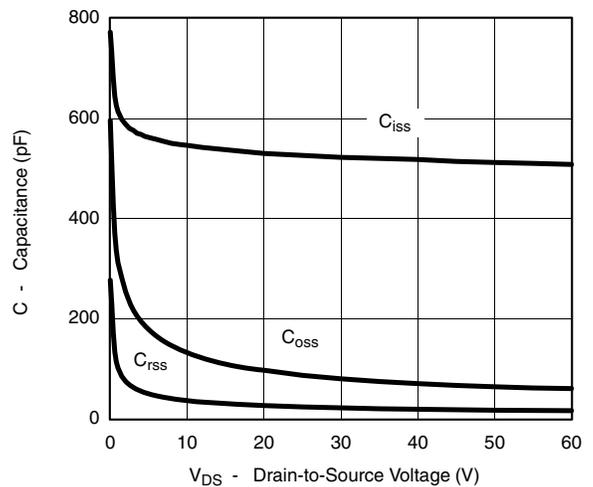
Output Characteristics



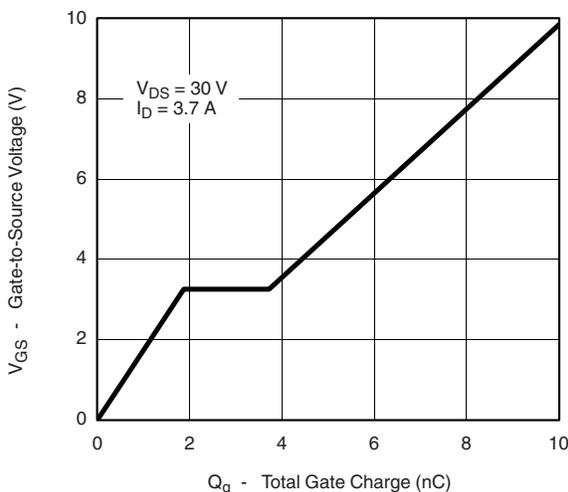
Transfer Characteristics



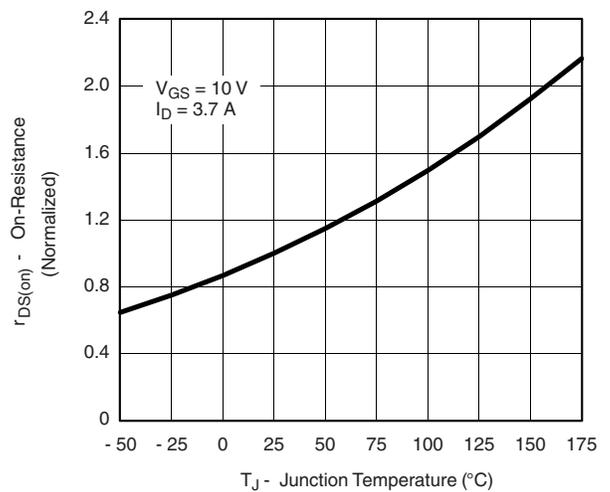
On-Resistance vs. Drain Current



Capacitance

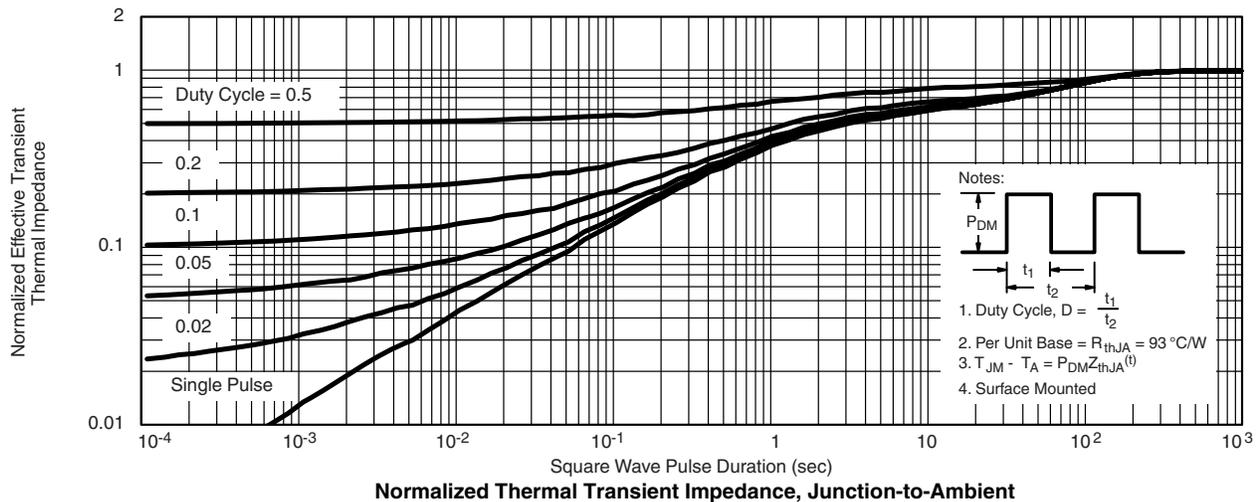
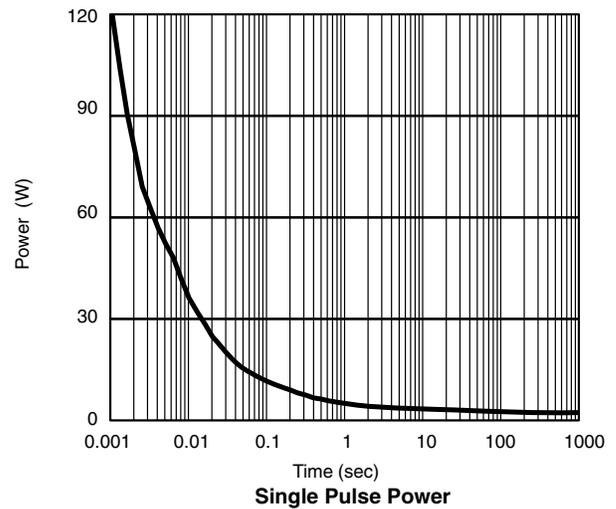
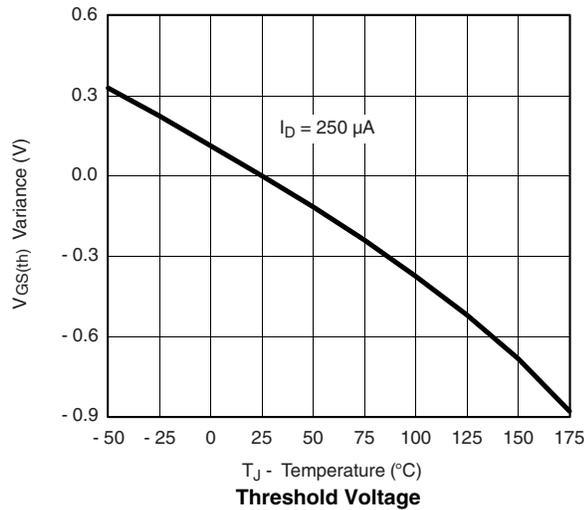
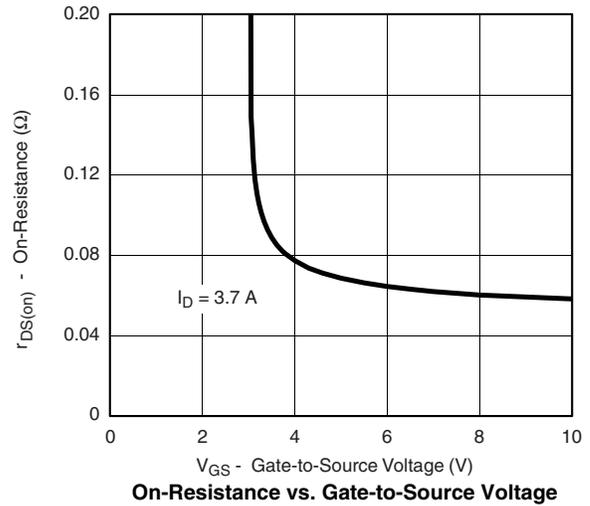
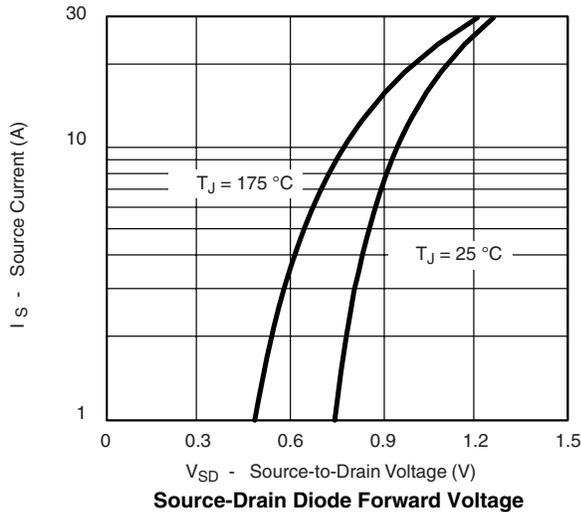


Gate Charge



On-Resistance vs. Junction Temperature

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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